N-Channel Power MOSFET

24 V, 9 A, 16 m Ω , Dual ECH8

Features

- Low ON-resistance
- 2.5 V Drive
- Common-drain Type
- Protection Diode in
- Built-in Gate Protection Resistor
- Best Suited for LiB Charging and Discharging Switch
- This Device is Pb-Free and are RoHS Compliant

Product & Package Information

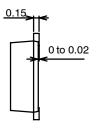
Package: ECH8JEITA, JEDEC: -

• Minimum Packing Quantity: 3,000 Pcs./Reel

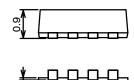
TopView

Unit : mm (typ) 7011A-003

2.9



ECH8655R-R-TL-H



0.07

2 : Gate1
3 : Source2
4 : Gate2
5 : Drain

1 : Source1

5 : Drain 6 : Drain 7 : Drain 8 : Drain

Bottom View

ECH8

Figure 1. Package Dimensions



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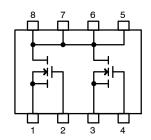


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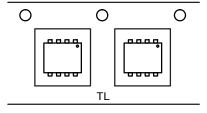
GENERIC MARKING DIAGRAM



ELECTRICAL CONNECTION



PACKING TYPE: TL



ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS at $T_A = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		24	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		9	Α
Drain Current (Pulse)	I _{DP}	PW ≤ 10 μs, duty cycle ≤ 1%	60	Α
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900 $\text{mm}^2 \times \text{0.8 mm})$ 1 unit	1.4	W
Total Dissipation	P _T	When mounted on ceramic substrate (900 $\text{mm}^2 \times 0.8 \text{ mm}$)	1.5	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$

			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D = 1 mA, V _{GS} = 0 V	24			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0V			1	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{GS} = \pm 8 \text{ V},$ $V_{DS} = 0 \text{ V}$			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} = 10 V, I _D = 1 mA	0.5		1.3	V
Forward Transfer Admittance	yfs	V _{DS} = 10 V, I _D = 4.5 A	4.8	8		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D = 4.5 A, V _{GS} = 4.5 V	10	13	16	mΩ
	R _{DS} (on)2	I _D = 4.5 A, V _{GS} = 4.0 V	10.5	13.5	16.5	mΩ
	R _{DS} (on)3	I _D = 4.5 A, V _{GS} = 3.1 V	11	15	20	mΩ
	R _{DS} (on)4	I _D = 2 A, V _{GS} = 2.5 V	13	18	24	mΩ
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		320		ns
Rise Time	t _r	- IGSLOIICUIL		1100		ns
Turn-OFF Delay Time	t _d (off)	1		2400		ns
Fall Time	t _f] [2100		ns

ELECTRICAL CHARACTERISTICS at $T_A = 25^{\circ}C$

			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Total Gate Charge	Qg	$V_{DS} = 10 \text{ V},$ $V_{GS} = 10 \text{ V},$ $I_{D} = 9 \text{ A}$		16.8		nC
Gate-to-Source Charge	Qgs	$I_D = 9 A$		1.6		nC
Gate-to-Drain "Miller" Charge	Qgd]		4.8		nC
Diode Forward Voltage	V _{SD}	I _S = 9 A, V _{GS} = 0 V		0.8	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit

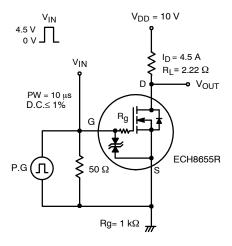


Figure 2. Switching Time Test Circuit

ORDERING INFORMATION

Device	Package	Shipping	Memo
ECH8655R-R-TL-H	ECH8	3,000 pcs./reel	Pb Free and Halogen Free

TYPICAL CHARACTERISTICS

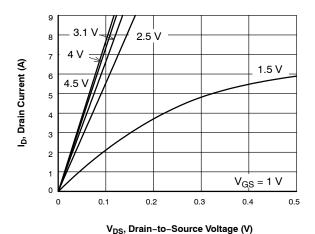
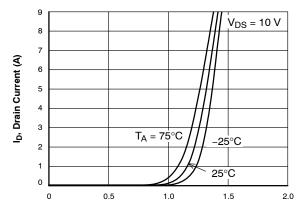


Figure 3. I_D - V_{DS}



V_{GS}, Gate-to-Source Voltage (V)

Figure 4. I_D - V_{GS}

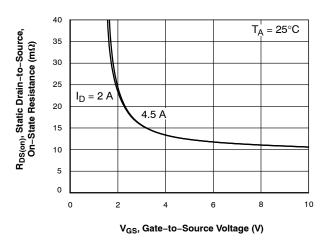


Figure 5. $R_{DS(on)} - V_{GS}$

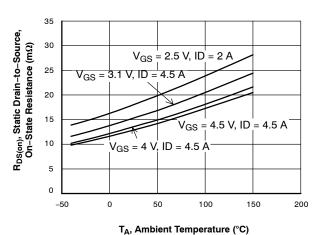


Figure 6. R_{DS(on)} - T_A

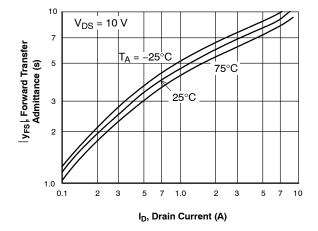


Figure 7. |yfs| - I_D

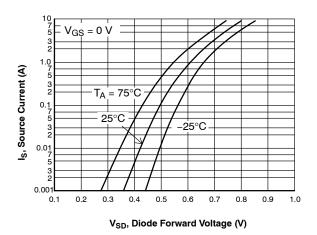


Figure 8. I_S - V_{SD}

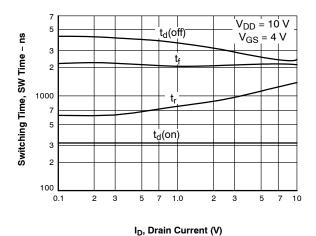
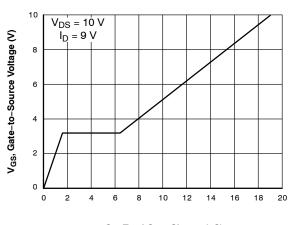
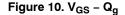
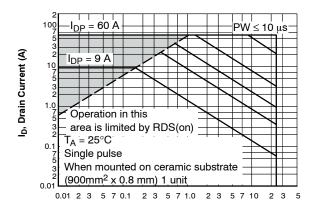


Figure 9. SW Time - I_D



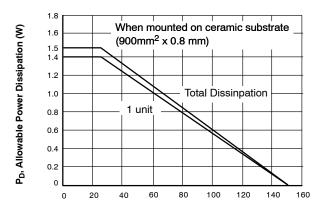
Qg, Total Gate Charge (nC)





V_{DS}, Drain-to-Source Voltage (V)

Figure 11. ASO



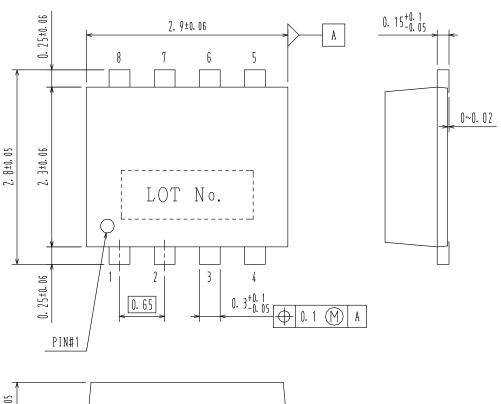
 T_A , Ambinet Temperature (°C)

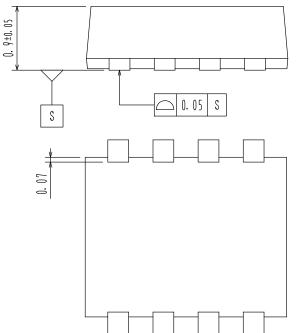
Figure 12. P_D – T_A

Since the ECH8655R-R-TL-H is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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DATE 31 MAR 2012





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